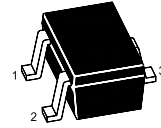
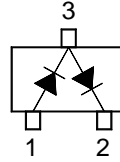


1SS372W

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

- High speed switching



SOT-323 Plastic Package
Marking Code: ME

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	200	mA
Peak Forward Surge Current ($t_p = 10\text{ ms}$)	I_{FSM}	1	A
Power Dissipation	P_d	100	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.3 0.5	V
Reverse Current at $V_R = 10\text{ V}$	I_R	20	μA
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_T	40	pF

